Application Number: 09/696,232 Attorney Docket Number: 07553.0017

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions and listings of claims in the application:

Claim 1 (currently amended): An etching method for etching an etching target film formed on a substrate placed inside an airtight processing chamber by Inducing a processing gas into said processing chamber, wherein;

said processing gas contains N_2 and at least one of C_4F_8 and CF_4 at least a C_3F_7 gas and N_2 , but does not contain O_2 ; and

said etching target film is constituted of an upper organic film containing Si and a lower formed on an SiO₂ film.

Claim 2 (original): An etching method according to claim 1, wherein: said organic film containing Si is constituted of SiO₂ containing C and H.

Claim 3 (original): An etching method according to claim 1, wherein:

the dielectric constant of said organic film containing Si is equal to or lower than

3.0.

Claim 4 (original): An etching method according to claim 1, wherein: said organic film containing Si is an organic polysiloxane film.

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Claim 5 (original): An etching method according to claim 1, wherein: said processing gas further contains Ar.

Claims 6-12 (canceled).

Claim 13 (currently amended): An etching method according to claim 1, wherein; said processing gas contains at least C_*F_y gas is CF_4 and N_2 .

Claim 14 (previously presented): An etching method according to claim 13, wherein; the flow rate ratio of CF_4 and N_2 in said processing gas is essentially set within a range of 1 \leq (N_2 flow rate / CF_4 flow rate) \leq 4.

Claims 15 and 16 (canceled).

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